

# Silicon N-Channel MOS FET

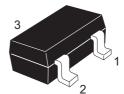
REJ03G0811-0200 (Previous ADE-208-1170) Rev.2.00 Aug.10.2005

## Application

VHF amplifier

### Outline

RENESAS Package code: PLSP0003ZB-A (Package name: MPAK)



- 1. Gate 2. Drain
- 3. Source



# ASSOUNCEMANTUNHRAPPINGS

|                                 |                     |             | $(Ta = 25^{\circ}C)$ |
|---------------------------------|---------------------|-------------|----------------------|
| Item                            | Symbol              | Ratings     | Unit                 |
| Drain to source voltage         | V <sub>DSX</sub> *1 | 20          | V                    |
| Gate to source voltage          | V <sub>GSS</sub>    | ±5          | V                    |
| Drain current                   | ID                  | 30          | mA                   |
| Gate current                    | l <sub>G</sub>      | ±1          | mA                   |
| Channel power dissipation       | Pch                 | 150         | mW                   |
| Channel temperature             | Tch                 | 150         | °C                   |
| Storage temperature             | Tstg                | -55 to +150 | °C                   |
| Note: $1 \sqrt{2} - 4 \sqrt{2}$ |                     |             |                      |

Note: 1.  $V_{GS} = -4 V$ 

## **Electrical Characteristics**

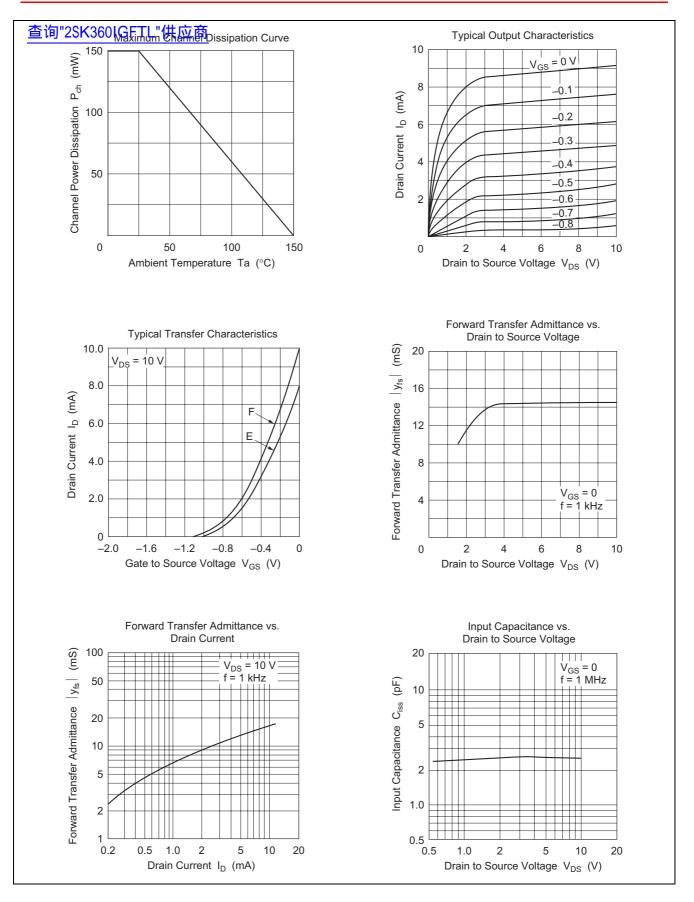
 $(Ta = 25^{\circ}C)$ 

| ltem                              | Symbol                          | Min | Тур  | Max  | Unit | Test conditions                               |
|-----------------------------------|---------------------------------|-----|------|------|------|---|
| Drain to source breakdown voltage | V <sub>(BR)DSX</sub>            | 20  | _    | _    | V    | $I_D = 100 \ \mu A, V_{GS} = -4 \ V$          |
| Gate cutoff current               | I <sub>GSS</sub>                |     |      | ±20  | nA   | $V_{GS} = \pm 5 \text{ V},  V_{DS} = 0$       |
| Drain current                     | I <sub>DSS</sub> * <sup>1</sup> | 6   |      | 12   | mA   | $V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0$   |
| Gate to source cutoff voltage     | V <sub>GS(off)</sub>            | 0   |      | -2.0 | V    | $V_{DS} = 10 \text{ V}, I_D = 10 \mu\text{A}$ |
| Forward transfer admittance       | y <sub>fs</sub>                 | 8   | 14   |      | mS   | $V_{DS} = 10 V, V_{GS} = 0,$                  |
|                                   |                                 |     |      |      |      | f = 1 kHz                                     |
| Input capacitance                 | Ciss                            | _   | 2.5  | _    | pF   | $V_{DS} = 10 V, V_{GS} = 0,$                  |
| Output capacitance                | Coss                            |     | 1.6  |      | pF   | f = 1 MHz                                     |
| Reverse transfer capacitance      | Crss                            |     | 0.03 |      | pF   | ]   |
| Power gain                        | PG                              |     | 30   |      | dB   | $V_{DS} = 10 V, V_{GS} = 0,$                  |
| Noise figure                      | NF                              |     | 2.0  |      | dB   | f = 100 MHz                                   |

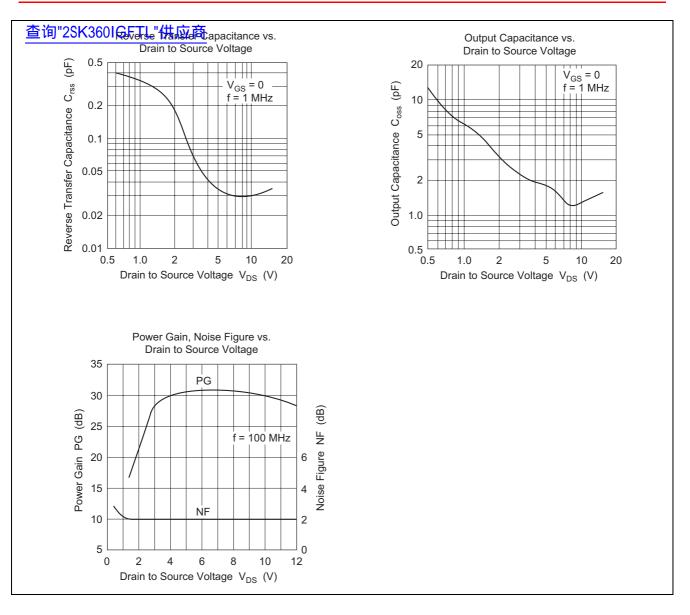
Note: 1. The 2SK360 is grouped by  $I_{\text{DSS}}$  as follows.

| Grade            | E       | F       |
|------------------|---------|---------|
| Mark             | IGE     | IGF     |
| I <sub>DSS</sub> | 6 to 10 | 8 to 12 |



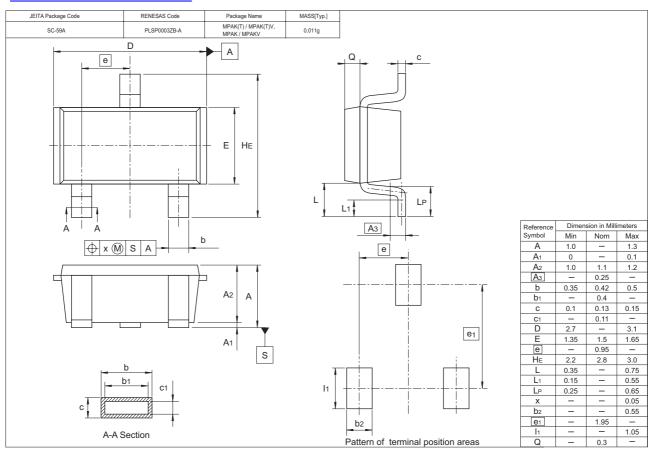








## Package Dimensio供 前



## **Ordering Information**

| Part Name   | Quantity | Shipping Container              |
|-------------|----------|---------------------------------|
| 2SK360IGETL | 3000     | φ178mm Reel , 8mm Emboss Taping |
| 2SK360IGFTL | 3000     | φ178mm Reel , 8mm Emboss Taping |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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